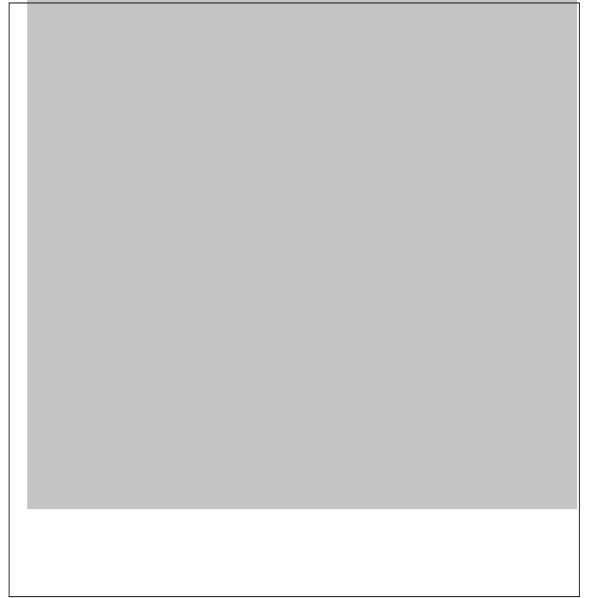


HC! 'D`UghjW!9bWUdg i`UhY`ACG : 9HG

ÁŠ[, ÁÜÖÙÇ[}DÁÁ
Š[, ^!ÁÖæ]æ&æcæ }&^•Á
ÁŠ[, ^!ÁVÁ [cæ]ÁÖæc^ÁÖ@æ! *^Á
Vá* @c^!ÁXÜÖÁÙ]^&á-á&æcá []•Á
ÁÆçæ]æ }&@^ÁÖ}^! *^ÁÙ]^&á-á^áÁ
Í€XÁPÈÖ@æ }^!Á T U Ò Ø V



A5L=A I A`F5H=B ; G`5B8`7<5F57H9F=GH=7G

O GÍ »Ô Æ { àâ^}c V^ {]^!æç~!^ Ç~ }|^••



B*\$'

F5H-B ; G 5B8 7<5F57H9F=GH=7 7 I FJ9G

ACG: 9H`9@97HF=75@`7<5F57H9F=GH=7G`V_{CE}MGÍ CÁ` }|[^]••Á[c@^! , á•^Á•] ^&â-â^â

DUfU a YhYf	Gm a Vc`	HYgh`7 cbX]h]cb	A]b	Hmd	AUI	I b]hg
Gate-Body Leakage Current (note 4)	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
Drain-Source Breakdown Voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	600			V
Gate-Threshold Voltage	V _{GS(th)}		2.0		4.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			1	μA
Forward transconductance	g _{fs}	V _{DS} = 0V, I _D =2 A				S
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.25A			2.5	ô
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz			670	pF
Output Capacitance	C _{oss}				72	
Reverse Transfer Capacitance	C _{rss}				8.5	
Turn-On Delay Time (note 4)	t _{d(on)}	V _{DD} =300V, I _D =4.5 A, R _G =25			30	ns
Rise Time (note 4)	t _r				90	
Turn-Off Delay Time (note 4)	t _{d(off)}				85	
Fall Time (note 4)	t _f				100	
Forward on Voltage (note 4)	V _{SD}	V _{GS} =0V, I _S =4.5A			1.4	V

BchYg.`

1. E_{AS} condition: T_j=25 , V_{DD}=50V, R_G=25 , L=16mH, I_{AS}=5A
2. This test is performed with no heat sink at T_a=25 .
3. This test is performed with infinite heat sink at T_c=25 .
4. Pulse Test : Pulse Widthm300μs, Duty Cycle m2%.